

RT1P141X SERIES

<Transistor>

Transistor With Resistor
For Switching Application
Silicon PNP Epitaxial Type

DESCRIPTION

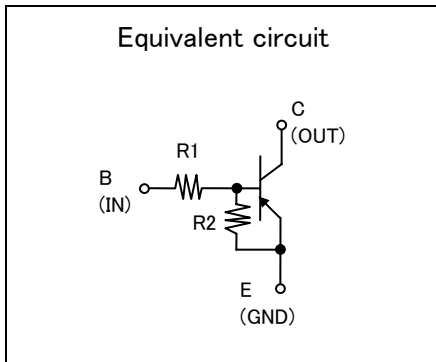
RT1P141X is a one chip transistor with built-in bias resistor, NPN type is RT1N141X.

FEATURE

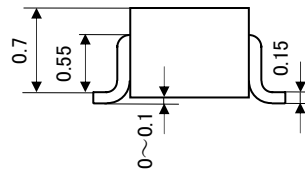
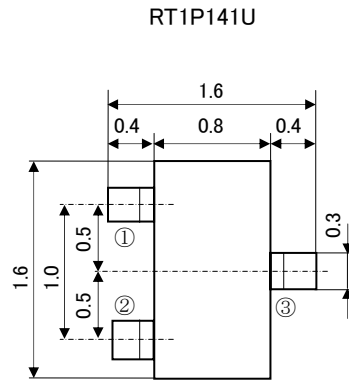
• Built-in bias resistor ($R1=10k\Omega, R2=10k\Omega$).

APPLICATION

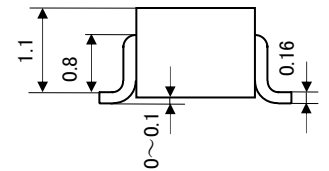
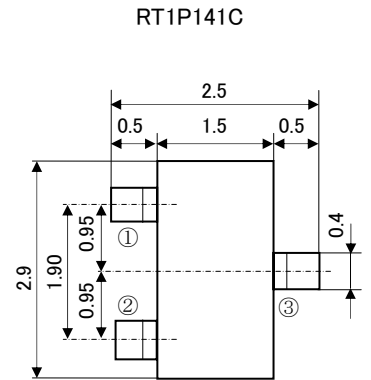
Inverted circuit, switching circuit, interface circuit, driver circuit.



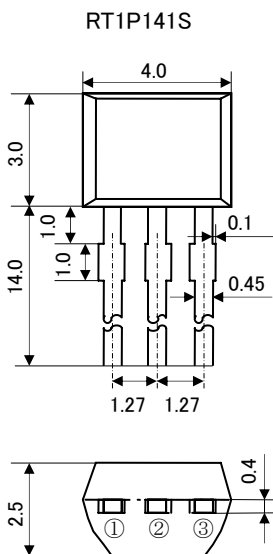
OUTLINE DRAWING UNIT : mm



JEITA: —
JEDEC: —
Terminal Connector
①: Base
②: Emitter
③: Collector

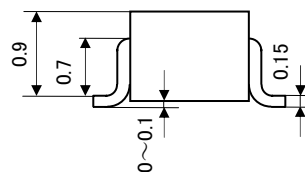
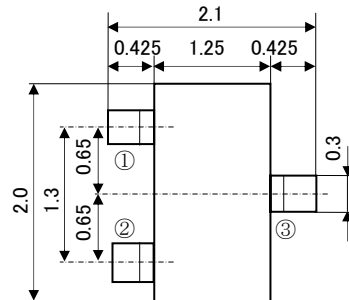


JEITA: SC-59
JEDEC: Similar to TO-236
Terminal Connector
①: Base
②: Emitter
③: Collector

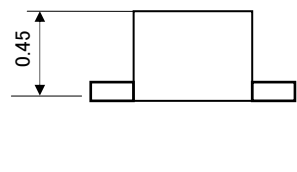
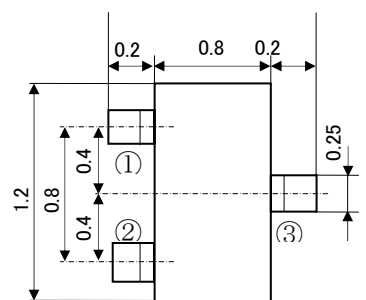


JEITA: —
JEDEC: —

①: Emitter
②: Collector
③: Base



JEITA: SC-70
JEDEC: —
Terminal Connector
①: Base
②: Emitter
③: Collector



JEITA: —
JEDEC: —
Terminal Connector
①: Base
②: Emitter
③: Collector

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MAXIMUM RATING (Ta=25°C)

SYMBOL	PARAMETER	RATING					UNIT
		RT1P141T	RT1P141U	RT1P141M	RT1P141C	RT1P141S	
V_{CBO}	Collector to Base voltage	-50					V
V_{EBO}	Emitter to Base voltage	-10					V
V_{CEO}	Collector to Emitter voltage	-50					V
I_C	Collector current	-100					mA
I_{CM}	Peak Collector current	-200					mA
P_C	Collector dissipation (Ta=25°C)	125(※)	125	150		450	mW
T_j	Junction temperature	+125		+150			°C
T_{stg}	Storage temperature	-55~+125			-55~+150		°C

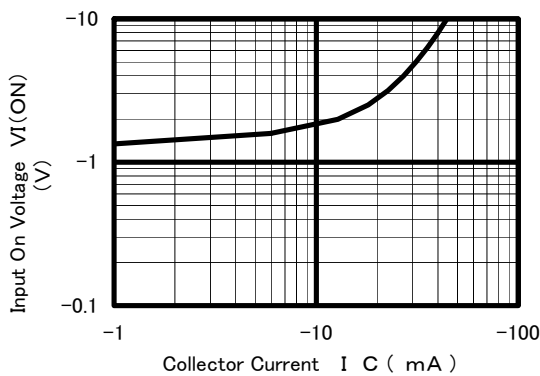
ELECTRICAL CHARACTERISTICS (Ta=25°C)

(※) package mounted on 9mm×19mm×1mm glass-epoxy substrate.

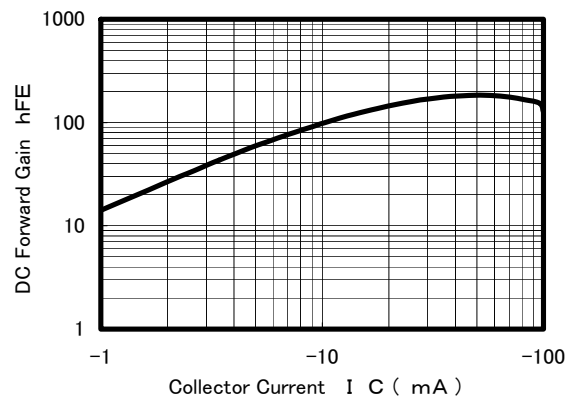
SYMBOL	PARAMETER	TEST CONDITION	LIMIT			UNIT
			MIN	TYP	MAX	
$V_{(BR)CEO}$	C to E break down voltage	$I_C = -100 \mu A, R_{BE} = \infty$	-50			V
I_{CBO}	Collector cut off current	$V_{CB} = -50V, I_E = 0$			-0.1	μA
h_{FE}	DC forward current gain	$V_{CE} = -5V, I_C = -10mA$	50			—
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -10mA, I_B = -0.5mA$		-0.1	-0.3	V
$V_{I(ON)}$	Input on voltage	$V_{CE} = -0.2V, I_C = -5mA$		-1.5	-3.0	V
$V_{I(OFF)}$	Input off voltage	$V_{CE} = -5V, I_C = -100 \mu A$	-0.8	-1.1		V
R_1	Input resistance		7.0	10	13	k Ω
R_2/R_1	Resistance ratio		0.9	1.0	1.1	
f_T	Gain band width product	$V_{CE} = -6V, I_E = 10mA$		150		MHz

TYPICAL CHARACTERISTICS

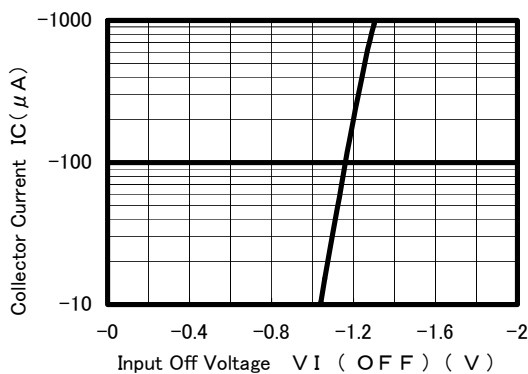
Input On Voltage - Collector Current



DC Forward Gain - Collector Current



Collector Current - Input Off Voltage





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